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Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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PHOTONIC Silicon Carbide (SiC), Ultra Violet (U.V.) Photodiode Type PDU-S102 DETECTORS INC. PACKAGE DIMENSIONS inch [mm] Ø.360 [Ø9.14] 171 [4.35] CATHODE Ø.237 [Ø6.01] .072 [1.83] – Ø.200 [Ø5.08] PIN CIRCLE Ø.017 [0.43] Ø.325 [8.24] 89° VIEWING CASE HEADER U.V. WINDOW CAP (WELDED) ANODE (CASE) .031 [0.80] .500 [12.7] MIN .0415 [1.054] CATHODE BOTTOM SIDE ANODE **TO-5 HERMETIC CAN PACKAGE** ACTIVE AREA = 1.0 mm² **FEATURES** DESCRIPTION **APPLICATIONS** • 0.14 A/W @ 280 nm The PDU-S102 is a SiC, planar passivated • Flame detectors U.V. photodiode. Spectral range from 200 • High shunt resistance U.V. sensors • 280 nm peak response nm to 400 nm with a 1.0 mm² active area. • U.V. monitors Packaged in a hermetic TO-5 with a U.V. • Short wavelength resp. • U.V. instrumentation transmitting window cap.

ADOCLOTE MAXIMOM TRATING (TA-23 O unless otherwise noted)							
PARAMETER	MIN	MAX	UNITS				
Reverse Voltage		20	V				
Storage Temperature	-55	+175	°C				
Operating Temperature Range	-40	+125	°C				
Soldering Temperature*		+240	°C				
Light Current		0.5	mA				
	PARAMETER Reverse Voltage Storage Temperature Operating Temperature Range Soldering Temperature*	PARAMETERMINReverse Voltage-55Storage Temperature-55Operating Temperature Range-40Soldering Temperature*-40	PARAMETERMINMAXReverse Voltage20Storage Temperature-55+175Operating Temperature Range-40+125Soldering Temperature*+240				

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

5		UV-B UV-A						
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2	50							1
RESPONSIVITY (mA/W)		r						
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SPECTRAL RESPONSE

*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
l sc	Short Circuit Current	H = 1 SUN, 360 nm		1.0		μA
I _D	Dark Current	$H = 0, V_{_{R}} = 1 V$		10	50	pА
R _{sh}	Shunt Resistance	$H = 0, V_{_{\rm R}} = 10 \text{ mV}$	100	200		$M\Omega$
TC R _{SH}	RSH Temp. Coefficient	$H = 0, V_{_{\rm R}} = 10 \text{ mV}$		-8		% / °C
C	Junction Capacitance	$H = 0, V_{_{\rm R}} = 0 V^{**}$		200	250	pF
 ∧range	Spectral Application Range	Spot Scan	200		400	nm
λр	Spectral Response - Peak	Spot Scan		280		nm
V _{BR}	Breakdown Voltage	I = 10 µµA	10	30		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		1.0x10 ⁻¹³		W/ √Hz
tr	Response Time	$RL = 1 K \Omega V_{R} = 10 V$		50	100	nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. ** f = 1MHz [FORM NO. 100-PDU-S102 REV N/C]